

**Maximum Ratings** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 4) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-2.5	A
		T <sub>A</sub> = +70°C		-2.0	
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	-3.5	A
		T <sub>A</sub> = +70°C		-2.8	
Pulsed Drain Current ( <b>Note 6</b> )			I <sub>DM</sub>	-12	A
Maximum Continuous Body Diode Forward Current (Note 5)			I <sub>S</sub>	-1.8	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P <sub>D</sub>	0.92	W
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.47	W
Thermal Resistance, Junction to Ambient (Note 4)	R <sub>θJA</sub>	136	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	84	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current @T <sub>C</sub> = +25°C	I <sub>DSS</sub>	-	-	-1	μA	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.4	-0.6	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	-	55	70	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -1A
			70	90		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -1A
			90	110		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -1A
			110	150		V <sub>GS</sub> = -1.5V, I <sub>D</sub> = -1A
Forward Transfer Admittance	Y <sub>fs</sub>	-	12	-	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1A
Diode Forward Voltage (Note 5)	V <sub>SD</sub>	-	-0.7	-1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	-	210	-	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	-	92	-	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	-	38	-	pF	
Series Gate Resistance	R <sub>G</sub>	-	5.3	-	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (-4.5V)	Q <sub>g</sub>	-	2.9	-	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -1A
Gate-Source Charge	Q <sub>gs</sub>	-	0.3	-	nC	
Gate-Drain Charge	Q <sub>gd</sub>	-	0.5	-	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	-	7.3	-	ns	V <sub>DD</sub> = -10V, V <sub>GS</sub> = -4.5V, I <sub>DS</sub> = -1A, R <sub>G</sub> = 20Ω
Turn-On Rise Time	t <sub>r</sub>	-	14.0	-	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	-	42.6	-	ns	
Turn-Off Fall Time	t <sub>f</sub>	-	32	-	ns	

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout.
  - Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.
  - 300ms pulse, pulse duty cycle ≤ 2%.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

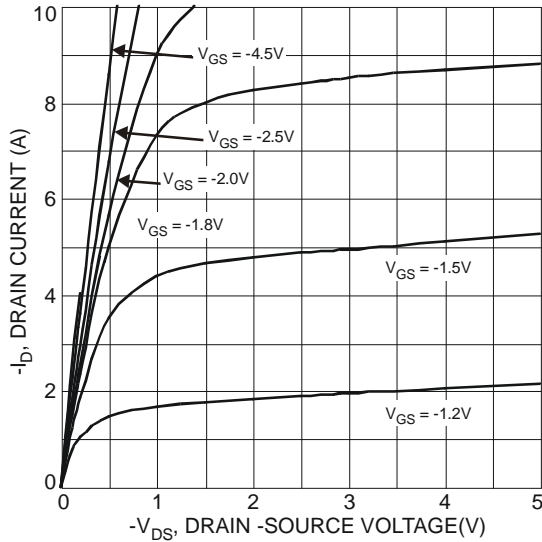


Fig. 1 Typical Output Characteristics

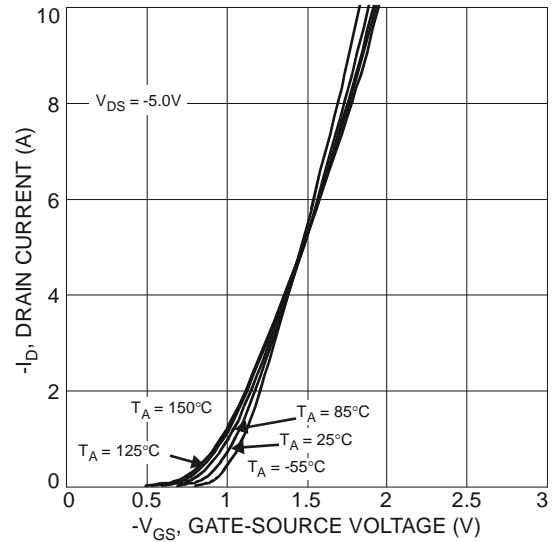


Fig. 2 Typical Transfer Characteristics

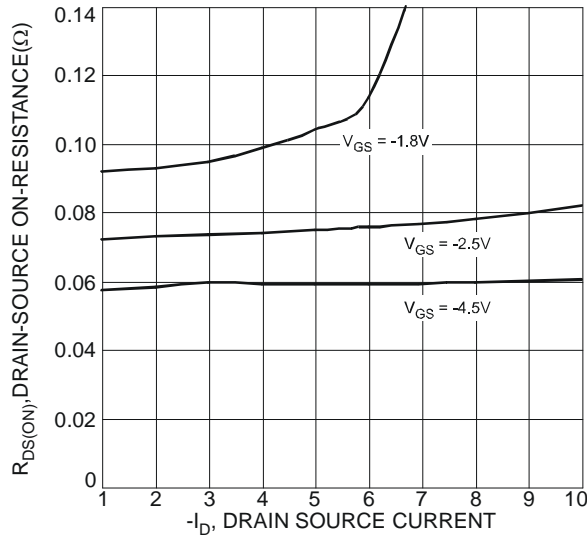


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

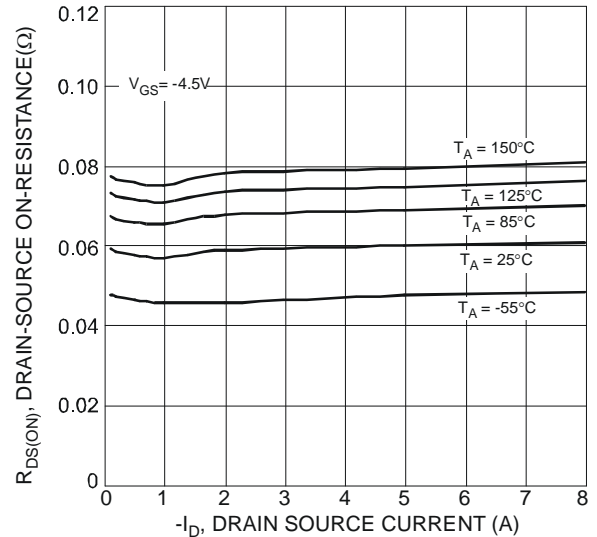


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

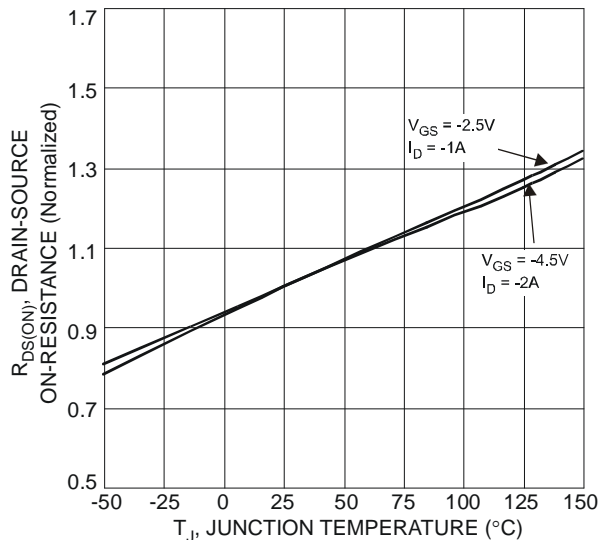


Fig. 5 On-Resistance Variation with Temperature

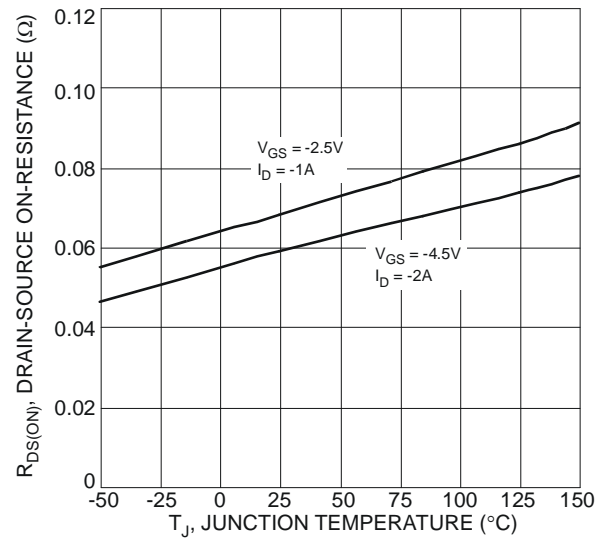


Fig. 6 On-Resistance Variation with Temperature

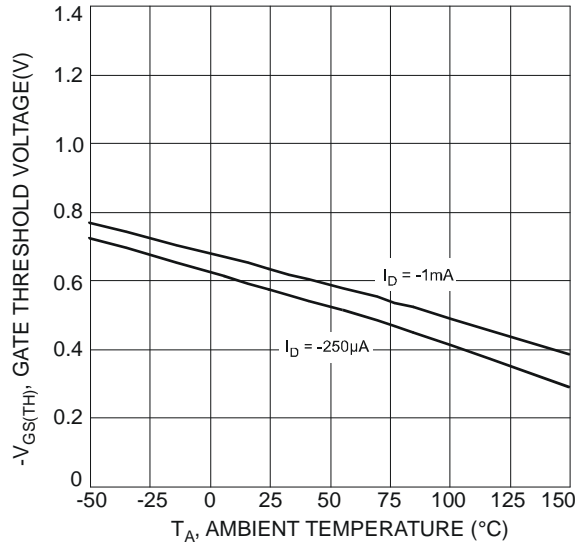


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

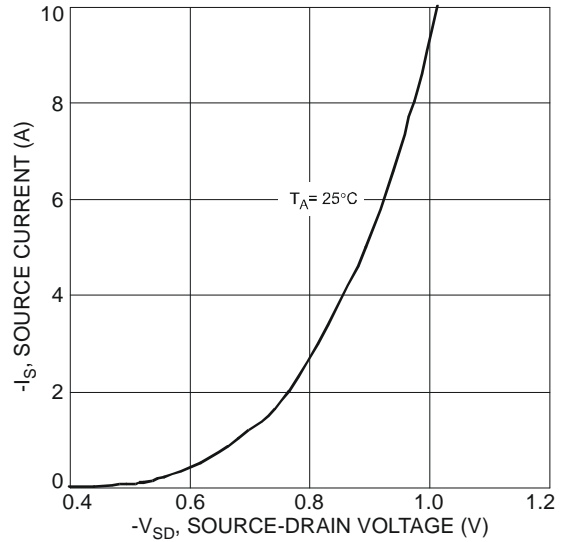


Fig. 8 Diode Forward Voltage vs. Current

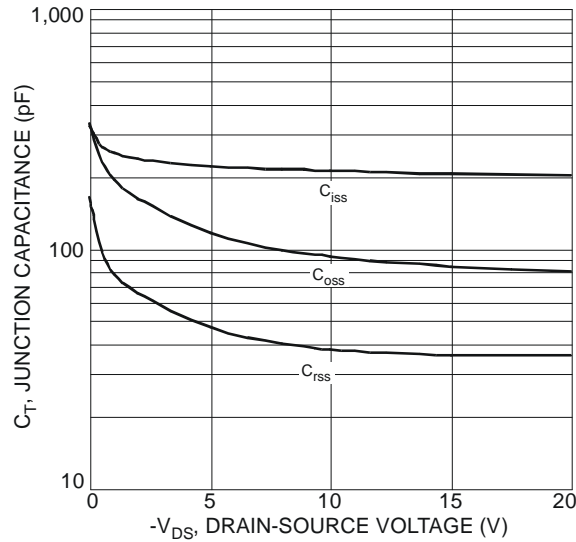


Fig. 9 Typical Junction Capacitance

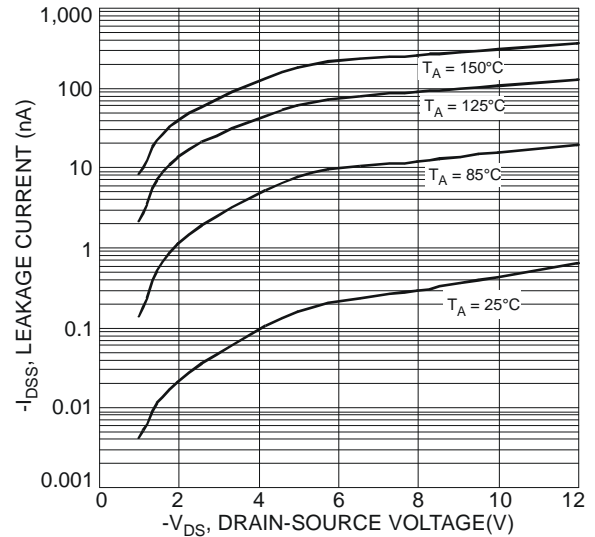


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

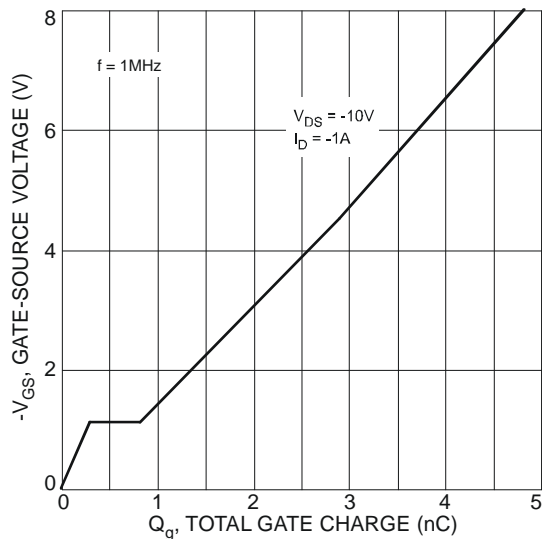


Fig. 11 Gate-Charge Characteristics

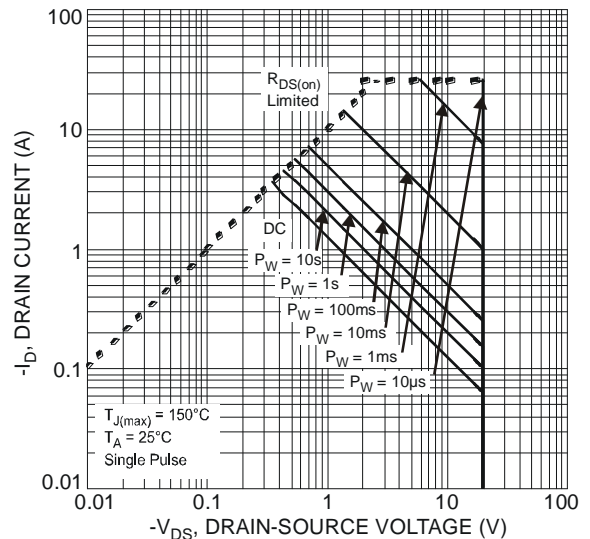


Fig. 12 SOA, Safe Operation Area

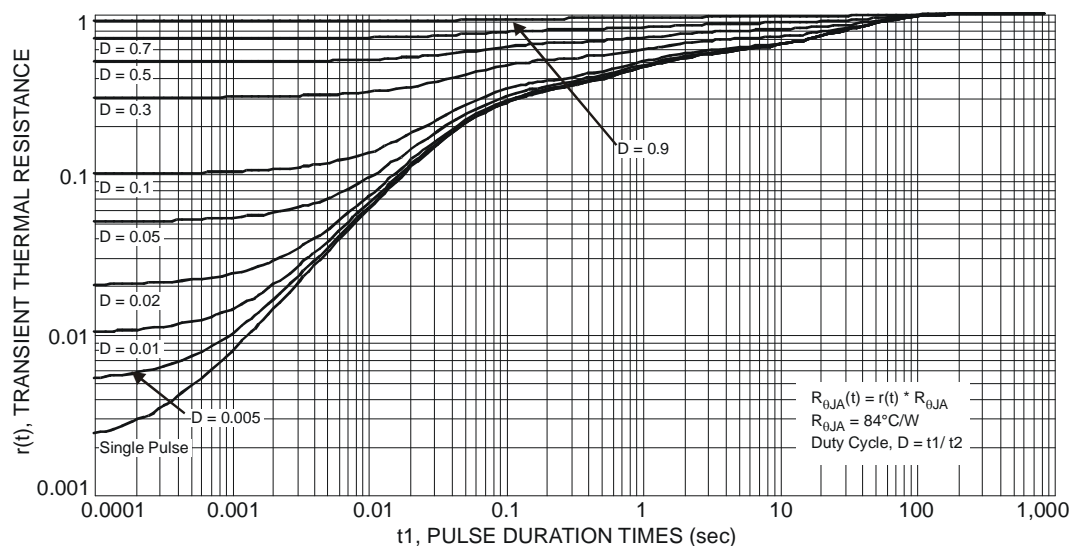
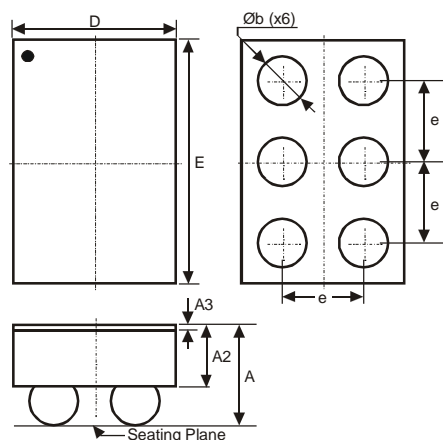


Fig. 13 Transient Thermal Resistance

## Package Outline Dimensions

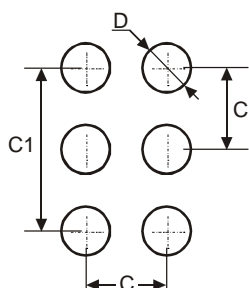
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-WLB1510-6			
Dim	Min	Max	Typ
D	0.90	1.00	1.00
E	1.40	1.50	1.50
A	—	0.62	—
A2	—	—	0.38
A3	0.020	0.030	0.025
b	0.27	0.37	0.32
e	—	—	0.50
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.50
C1	1.00
D	0.25

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